

In the Claims

CLAIMS

Claims 1-54 (Canceled).

55. (Withdrawn) A semiconductor construction of an isolation region comprising:

a semiconductor substrate having an opening extending partially therein, the substrate forming a first sidewall periphery of the opening;

a first masking layer formed over the semiconductor substrate and comprising a second sidewall periphery of the opening;

a second masking layer formed over the first masking layer and comprising a third sidewall periphery of the opening; and

wherein the second sidewall periphery is laterally spaced from the first and third sidewall peripheries, and wherein at least a portion of the third sidewall periphery is angled relative an other portion of the third sidewall periphery.

56. (Withdrawn) The semiconductor construction of claim 55 further comprising an insulative material partially filling the opening.

57. (Withdrawn) The semiconductor construction of claim 55 wherein the first masking layer comprises silicon dioxide and the second masking layer comprises silicon nitride.

58. (Withdrawn) The semiconductor construction of claim 55 further comprising an insulative material formed along the first sidewall periphery of the opening.

59. (Withdrawn) The semiconductor construction of claim 55 further comprising:

a first insulative material partially filling the opening; and

a second insulative material formed over the first insulative material.

60. (Withdrawn) The semiconductor construction of claim 55 wherein the angled portion of the third sidewall periphery forms a facet.

61. (Withdrawn) The semiconductor construction of claim 55 wherein the construction comprises an intermediate construction of an isolation region.

62. (Withdrawn) A semiconductor construction of an isolation region comprising:

a semiconductor substrate having a trench extending partially therein, the substrate forming a first sidewall periphery of the trench;

a first masking layer formed over the semiconductor substrate and comprising a second sidewall periphery of the trench; and

a second masking layer formed over the first masking layer and comprising a third sidewall periphery of the trench, the third sidewall periphery comprising a first edge substantially aligned with the first sidewall periphery and a second edge laterally spaced from the first sidewall periphery.

63. (Withdrawn) The semiconductor construction of claim 62 wherein the construction comprises an intermediate construction of an isolation region.

64. (Withdrawn) The semiconductor construction of claim 62 wherein the second sidewall periphery is substantially aligned with the first sidewall periphery.

65. (Withdrawn) The semiconductor construction of claim 62 further comprising an insulative material partially filling the trench.

66. (Withdrawn) The semiconductor construction of claim 62 wherein the first masking layer comprises silicon dioxide and the second masking layer comprises silicon nitride.

67. (Withdrawn) The semiconductor construction of claim 62 further comprising an insulative material formed along the first sidewall periphery of the trench.

68. (Withdrawn) The semiconductor construction of claim 62 further comprising:

a first insulative material partially filling the trench; and

a second insulative material formed over the first insulative material.

69. (Currently Amended) A semiconductor construction comprising:

a semiconductor substrate having a trench extending partially therein and upper surfaces adjacent the trench;

an oxide layer formed over the upper surfaces of the semiconductor substrate and having an uppermost surface; and

an insulative material filling the trench and having a portion outward of the trench and semiconductor substrate, the portion comprising an outermost upper surface elevationally above the uppermost surface of the oxide layer, the portion further comprising and sidewalls connecting the outermost upper surface with the oxide layer, ~~the connection between the sidewalls and the outermost upper surface comprising first curved corners, and the connection between the sidewalls and the oxide layer comprising second curved corners extending from elevationally above the oxide layer downward to the uppermost surface of the oxide layer~~ the sidewalls comprising first and second curved segments, the first curved segment extending from the outermost upper surface and comprising a first apex directed away from the substrate, and the second curved segment extending from the first curved segment to the oxide layer and comprising a second apex directed toward the substrate.

70. (Previously presented) The semiconductor construction of claim 69 wherein the insulative material comprises oxide.

71. (Previously presented) The semiconductor construction of claim 69 wherein the insulative material comprises a first insulative material partially filling the trench and a second insulative material formed over the first insulative material.

72. (Currently amended) The semiconductor construction of claim 69 further comprising a polysilicon layer formed against the uppermost surface of the oxide layer and against the portion of the insulative material.

73. (Currently amended) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the first curved ~~corners~~ segments of the portion are elevationally above and between the sidewalls of the trench.

74. (Currently amended) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the first curved ~~corners~~ segments of the portion are directly over the bottom wall of the trench.